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TriQSiC™ 1700V Silicon Carbide Power MOSFET G2

Features

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- &M 4
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Benefits

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1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

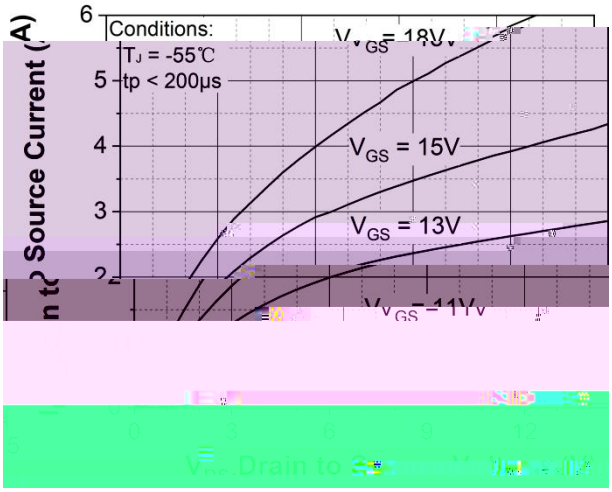
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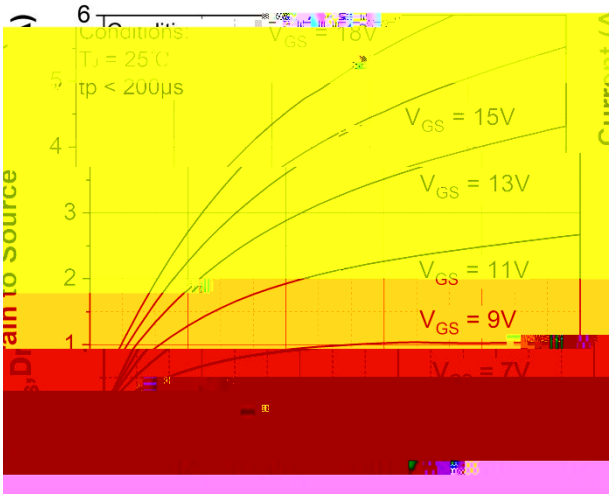
2.3 Switching characteristics

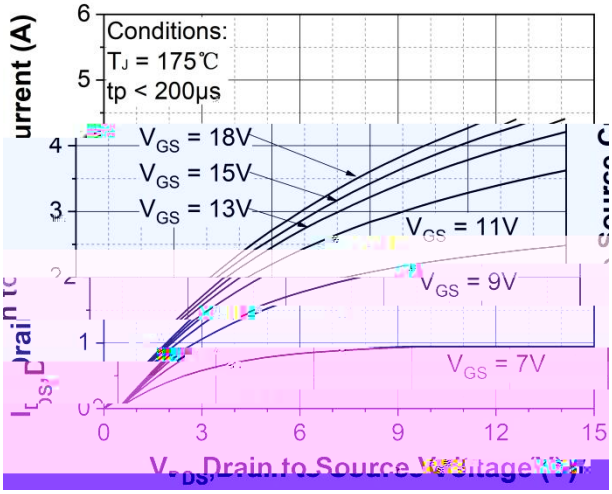
Table 6 Dynamic characteristics

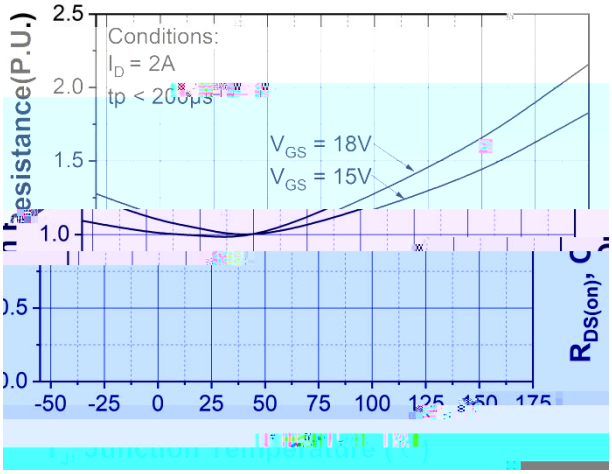
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

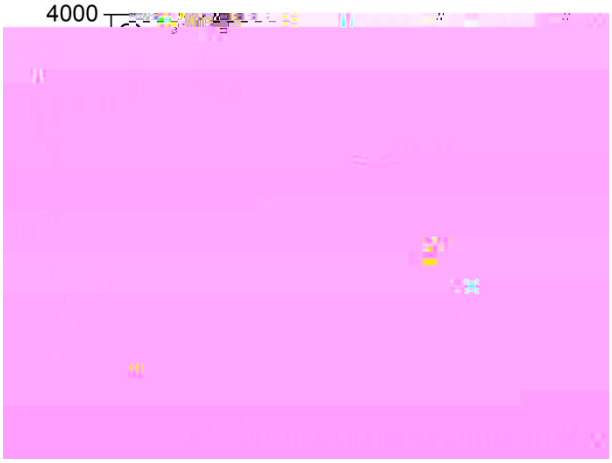
3 Electrical characteristic diagrams

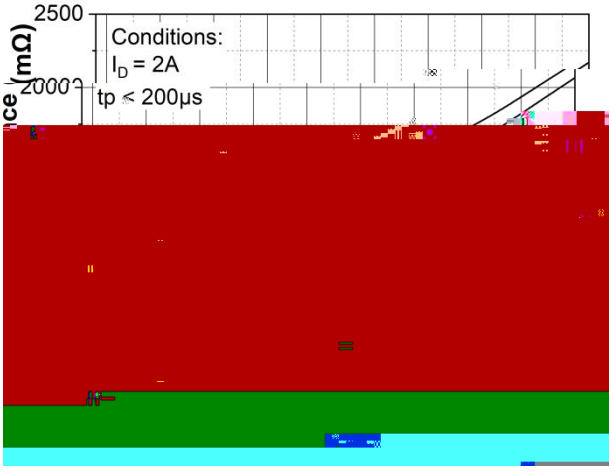










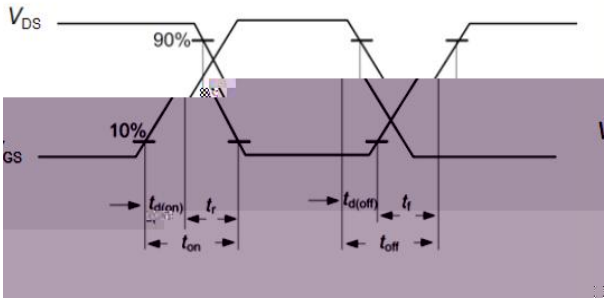


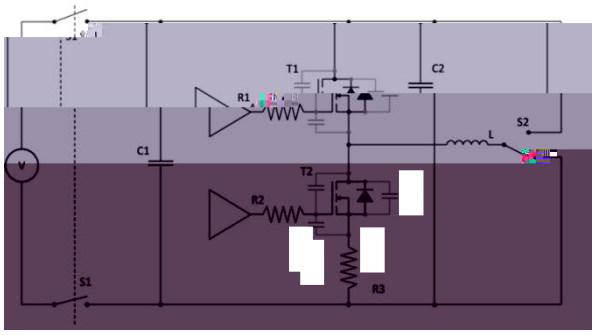
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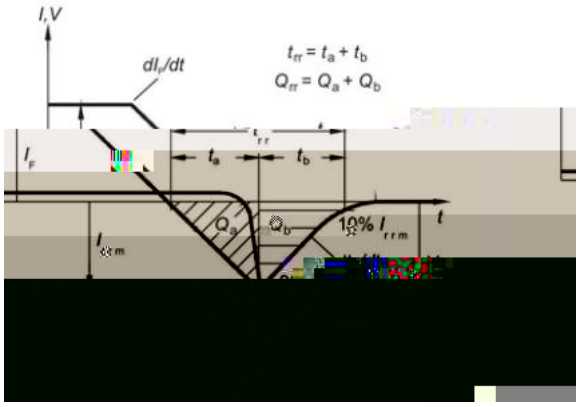
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5 Test conditions







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1700V SiC Power MOS[illegible]T

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-07-11	——	——
V01_01	2025-09-08	——	——
V01_02	2025-12-30	Final	——

Attention

Rohs compliance

REACH compliance

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